TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

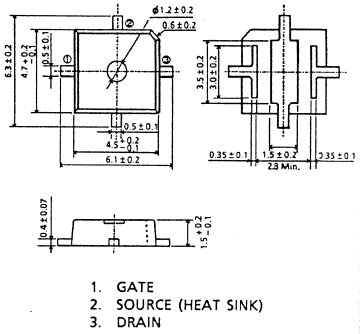
2SK3476

VHF- and UHF-band Amplifier Applications

(Note)The TOSHIBA products listed in this document are intended for high frequency Power Amplifier of telecommunications equipment.These TOSHIBA products are neither intended nor warranted for any other use.Do not use these TOSHIBA products listed in this document except for high frequency Power Amplifier of telecommunications equipment.

- Output power: P_O = 7.0 W (min)
- Gain: G_P = 11.4dB (min)
- Drain efficiency: η_D = 60% (min)

Unit: mm



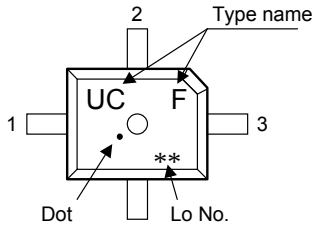
JEDEC	—
JEITA	—
TOSHIBA	2-5N1A

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	20	V
Gain-source voltage	V_{GSS}	±5	V
Drain current	I_D	3	A
Power dissipation	P_D (Note 1)	20	W
Channel temperature	T_{ch}	150	°C
Storage temperature range	T_{stg}	−45~150	°C

Note 1: Tc = 25°C (When mounted on a 1.6 mm glass epoxy PCB)

Marking



1. Gate
2. Source (heat sink)
3. Drain

Caution

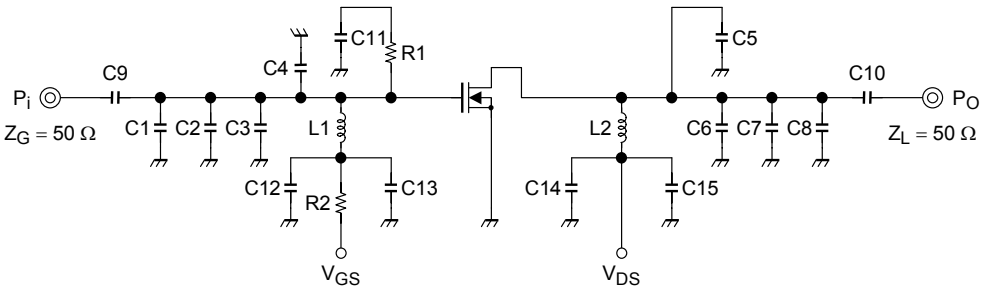
Please take care to avoid generating static electricity when handling this transistor.

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Drain cut-off current	I_{DSS}	V_{DS} = 20 V, V_{GS} = 0 V	—	—	5	μA
Gate-source leakage current	I_{GSS}	V_{GS} = 5 V	—	—	5	μA
Threshold voltage	V_{th}	V_{DS} = 7.2 V, I_D = 2 mA	0.55	1.05	1.55	V
Drain-source on-voltage	$V_{DS\ (ON)}$	V_{GS} = 10 V, I_D = 75 mA	—	18	—	mV
Forward transconductance	Y_{fs}	V_{DS} = 7.2 V, I_{DS} = 1 A	—	1	—	S
Input capacitance	C_{iss}	V_{DS} = 7.2 V, V_{GS} = 0 V, f = 1 MHz	—	53	—	pF
Output capacitance	C_{oss}	V_{DS} = 7.2 V, V_{GS} = 0 V, f = 1 MHz	—	49	—	pF
Output power	P_O	V_{DS} = 7.2 V, I_{idle} = 500 mA (V_{GS} = adjust), f = 520 MHz, P_i = 500 mW,	7	—	—	W
Drain efficiency	η_D		60	—	—	%
Power gain	G_P		11.4	—	—	dB
Low voltage output power	P_{OL}	V_{DS} = 6.0 V, I_{idle} = 500 mA (V_{GS} = adjust), f = 520 MHz, P_i = 500 mW,	5	—	—	W
Load mismatch	—	V_{DS} = 10 V, P_O = 7 W, V_{GS} = adjust, P_i = adjust, f = 520 MHz, VSWR LOAD 20:1 all phase	No degradation			

Note 1: These characteristic values are measured using measurement tools specified by Toshiba.

Output Power Test Fixture
(Test Condition: f = 520 MHz, V_{DS} = 7.2 V, I_{idle} = 500 mA, P_i = 500 mW)

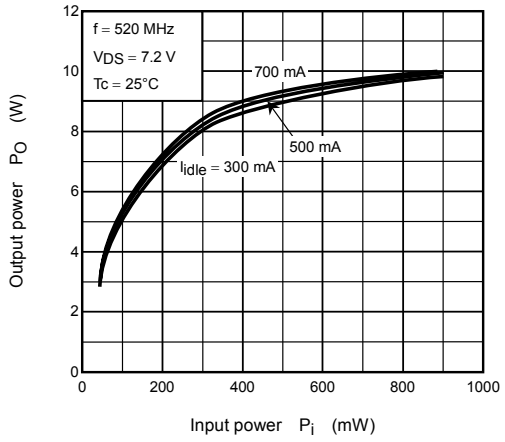


C1: 15 pF
C2: 11 pF
C3: 9 pF
C4: 30 pF
C5: 30 pF
C6: 11 pF
C7: 8 pF
C8: 9 pF
C9: 2200 pF
C10: 2200 pF
C11: 2200 pF
C12: 10000 pF
C13: 10 μF
C14: 10000 pF
C15: 10 μF

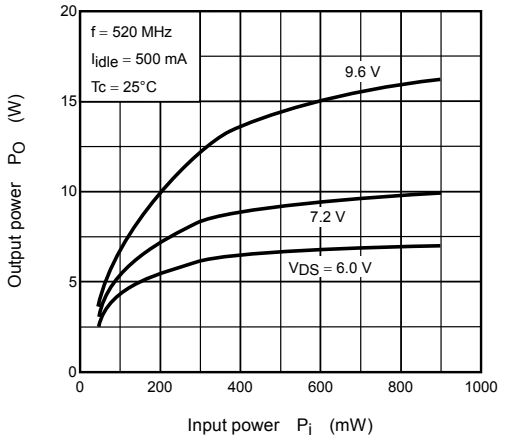
L1: ϕ0.6 mm enamel wire, 5.8ID, 4T
L2: ϕ0.6 mm enamel wire, 5.8ID, 8T

R1: 2.2 Ω
R2: 1.5 kΩ

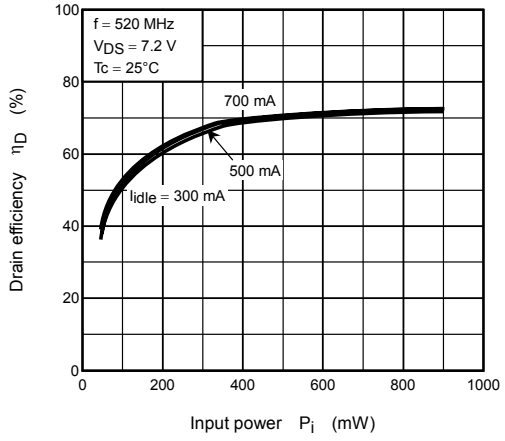
$P_O - P_i$



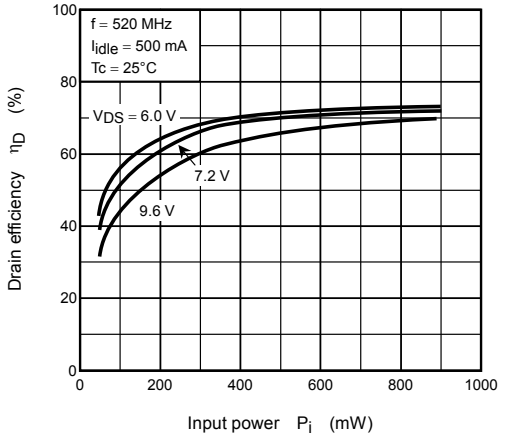
$P_O - P_i$



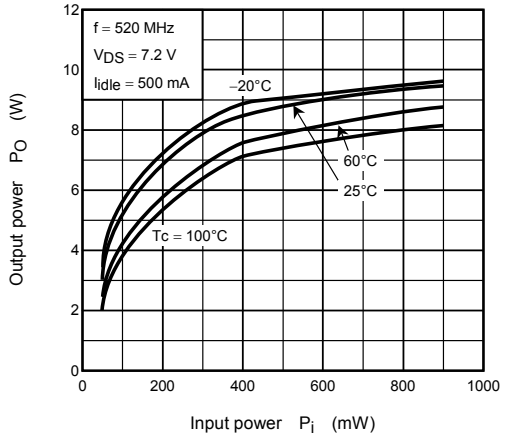
$\eta_D - P_i$



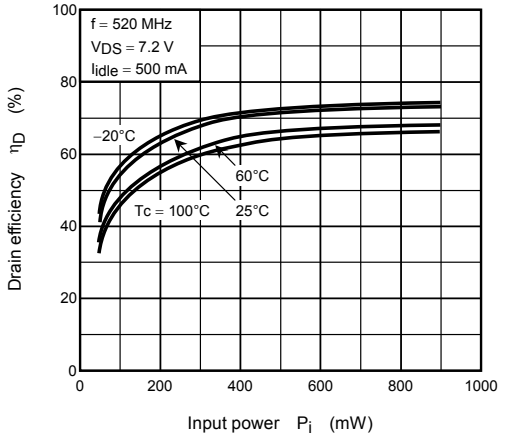
$\eta_D - P_i$



$P_O - P_i$



$\eta_D - P_i$



Note 2: These are only typical curves and devices are not necessarily guaranteed at these curves.

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